

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC3973B

DESCRIPTION

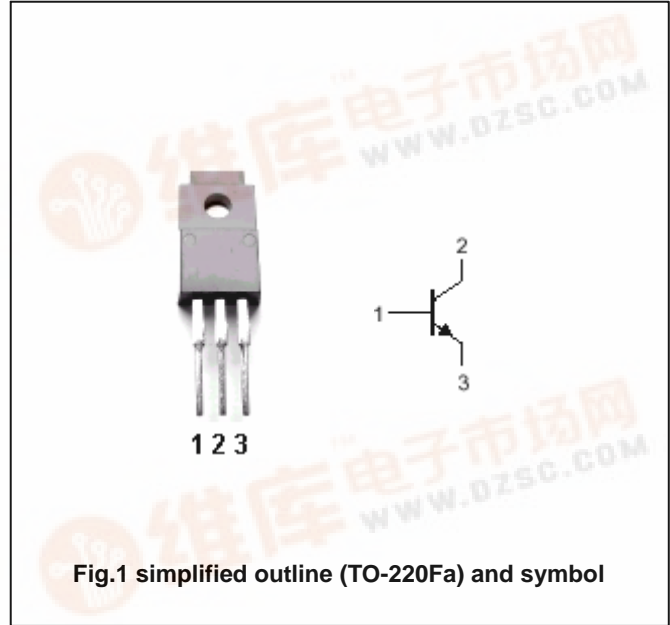
- With TO-220Fa package
- High voltage,high speed
- Wide area of safe operation

APPLICATIONS

- For high voltage,high speed switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25 °C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1000	V
V _{CEO}	Collector-emitter voltage	Open base	500	V
V _{EBO}	Emitter-base voltage	Open collector	8	V
I _C	Collector current (DC)		7	A
I _{CM}	Collector current-Peak		15	A
I _B	Base current (DC)		4	A
P _C	Collector power dissipation	T _a =25	2	W
		T _C =25	45	
T _j	Maximum operating junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	500			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A; I _B =0.8A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A; I _B =0.8A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =1000V; I _E =0			100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μA
h _{FE-1}	DC current gain	I _C =0.1A ; V _{CE} =5V	15			
h _{FE-2}	DC current gain	I _C =4A ; V _{CE} =5V	8			

固电半导体

INCHANGE SEMICONDUCTOR

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PACKAGE OUTLINE

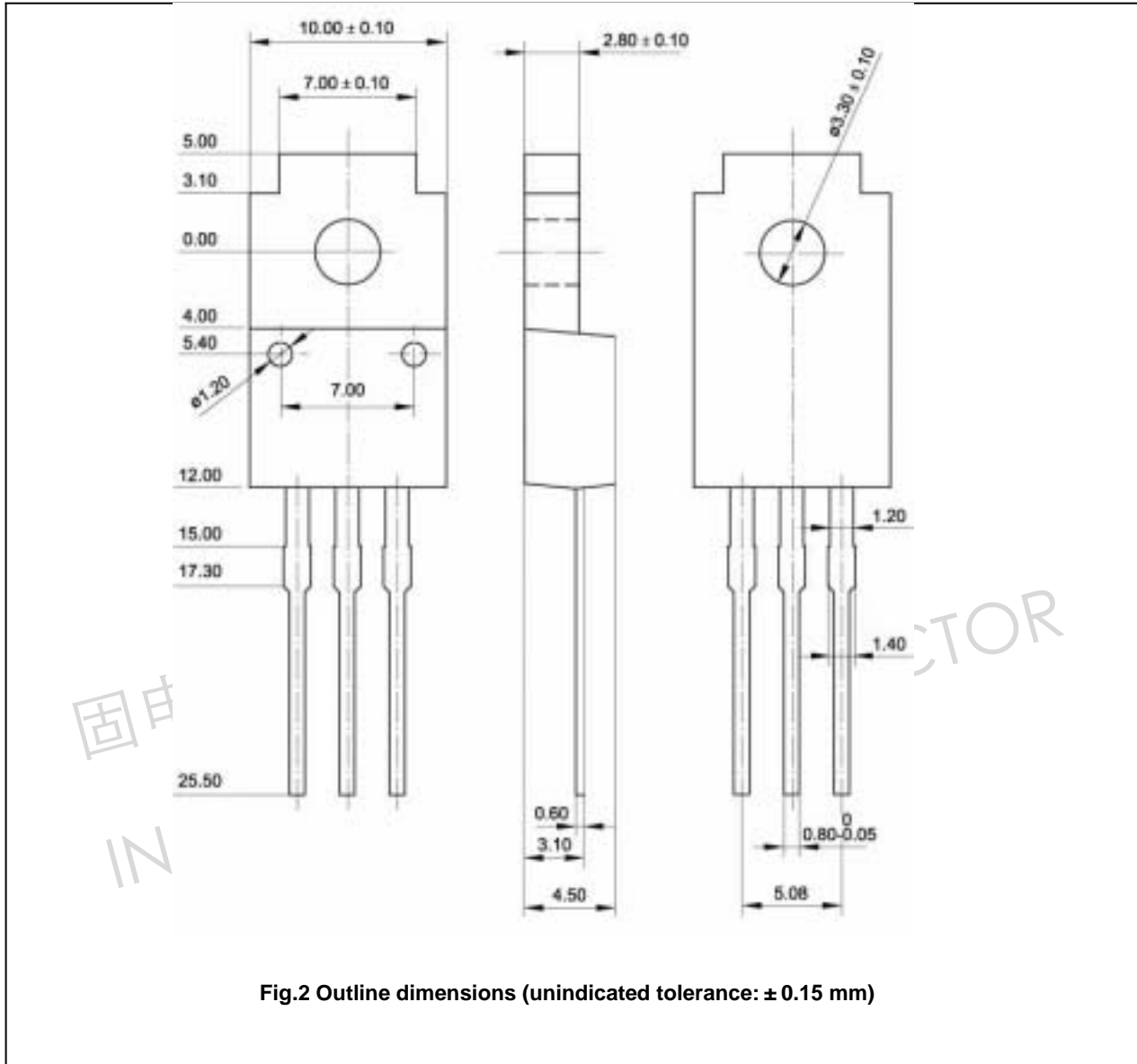


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)